

STTH20003TV

Ultrafast high voltage rectifier

Mian product characteristics

I _{F(AV)}	up to 2 x 100 A
V _{RRM}	300 V
T _j (max)	150° C
V _F (typ)	0.95 V
t _{rr} (max)	90 ns

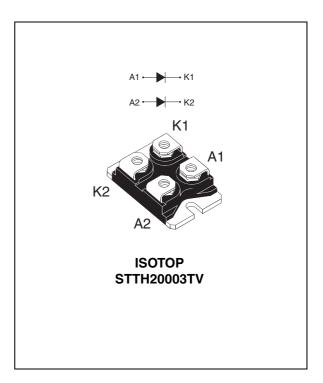
Features and benefits

- Combines highest recovery and reverse voltage performance
- Ultrafast, soft and noise-free recovery
- Package insulation voltage 2500 V_{rms}
- low inductance and low capacitance allow simpler layout

Description

Dual rectifiers suited for Switch Mode Power Supply and high frequency DC to DC converters.

Packaged in ISOTOP™, this device is intended for use in low voltage, high frequency inverters, free wheeling operation, welding equipment and telecom power supplies.



Order codes

Part number	Marking
STTH20003TV	STTH20003TV

Table 1. Absolute ratings (limiting values, per diode, $T_c = 25^{\circ}$ C unless otherwise stated)

Symbol	Parar	Value	Unit		
V _{RRM}	Repetitive peak reverse voltage			300	V
I _{F(RMS)}	RMS forward current			180	Α
I _{F(AV)} Average forward current	words forward current	$T_{c} = 85^{\circ} \text{ C } \delta = 0.5$	Per diode	r diode 100	
	Average lorward current	$I_{\rm C} = 65 \rm Co = 0.5$	Per device	200	Α
I _{FSM}	Surge non repetitive forward current $t_p = 10 \text{ ms sinusoidal}$			100	Α
T _{stg}	Storage temperature range	-55 to + 150	° C		
Tj	Maximum operating junction temperature			150	° C

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Characteristics STTH20003TV

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Table 2. Thermal resistance

Symbol	Parameter		Value (max).	Unit
В	lunation to coop	Per diode	0.55	
hth(j-c)	R _{th(j-c)} Junction to case		0.35	°C/W
R _{th(c)}	Coupling		0.1	

When diodes 1 and 2 are used simultaneously:

 $\Delta \text{ Tj(diode 1)} = P(\text{diode 1}) \times R_{\text{th(j-c)}}(\text{Per diode}) + P(\text{diode 2}) \times R_{\text{th(c)}}$

Table 3. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Тур	Max.	Unit
I _R ⁽¹⁾	Reverse leakage	T _j = 25° C	V _B = 300 V			200	μΑ
'R'	^{'R'} current	T _j = 125° C	v _R – 300 v		0.2	2	mA
V_(2)	V _F ⁽²⁾ Forward voltage drop	T _j = 25° C	I _E = 100 A			1.20	V
V _F \'/		T _j = 150° C	1F = 100 A		0.8	0.95	V

^{1.} Pulse test: $t_p = 5$ ms, $\delta < 2\%$

To evaluate the conduction losses use the following equation:

 $P = 0.75 \text{ x } I_{F(AV)} + 0.0020 I_{F^2(RMS)}$

Table 4. Dynamic characteristics (per diode)

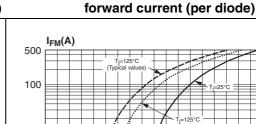
Symbol	Parameter	Test conditions			Тур	Max	Unit
	Reverse recovery		$I_F = 0.5 \text{ A}$ $I_{rr} = 0.25 \text{ A}$ $I_R = 1 \text{ A}$		55		
t _{rr}	time		$I_F = 1 \text{ A} dI_F/dt = -50 \text{ A/}\mu\text{s}$ $V_R = 30 \text{ V}$			90	ns
I _{RM}	Carron		$I_F = 100 \text{ A}$ $V_R = 200 \text{ V}$ $dI_F/dt = -200 \text{ A}/\mu\text{s}$			18	Α
S _{factor}	Softness factor	T _j = 125° C	$I_F = 100 \text{ A}$ $V_R = 200 \text{ V}$ $dI_F/dt = -200 \text{ A}/\mu\text{s}$		0.3		
t _{fr}	Forward recovery time	T _j = 25° C	I_F = 100 A dI_F/dt = 200 A/ μ s V_{FR} = 1.1 x V_{Fmax}			1400	ns
V _{FP}	Forward recovery voltage	T _j = 25° C	$I_F = 100 \text{ A}$ V_{Fmax} V_{Fmax}			5	٧

^{2.} Pulse test: $t_p = 380 \mu s$, $\delta < 2\%$

STTH20003TV **Characteristics**

Figure 2.

Figure 1. **Conduction losses versus** average forward current (per diode)



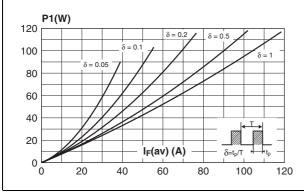
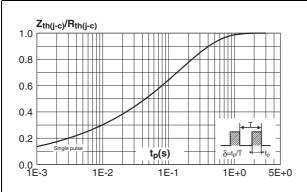


Figure 3. **Relative variation of thermal** impedance junction to case versus pulse duration

10 $V_{FM}(V)$ 8.0 0.6 1.0 1.2 1.4

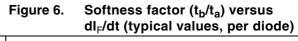
Forward voltage drop versus

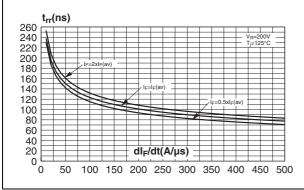
Figure 4. Peak reverse recovery current versus dl_F/dt (90% confidence, per diode)

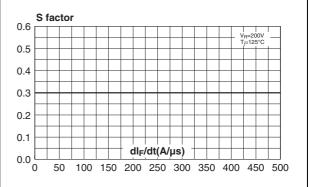


I_{RM}(A) 40 35 30 25 20 15 10 5 dl_F/dt(A/µs) 0 100 150 200 250 300 350 400 450 500

Figure 5. Reverse recovery time versus dl_F/dt (90% confidence, per diode)

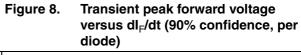


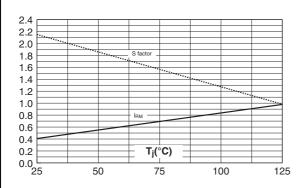




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Figure 7. Relative variations of dynamic parameters versus junction temperature (reference: $T_i = 125^{\circ}$ C)





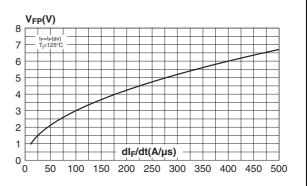
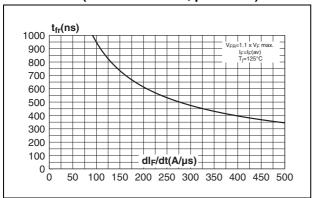


Figure 9. Forward recovery time versus dl_F/dt (90% confidence, per diode)



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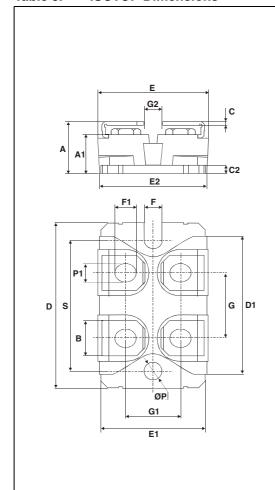
STTH20003TV Package information

2 Package information

Epoxy meets UL94, V0

Cooling method: by conduction (C)
Recommended torque value: 1.3 Nm
Maximum torque value: 1.5 Nm

Table 5. ISOTOP Dimensions



	Dimensions					
Ref.	Millim	neters	Inc	hes		
	Min.	Max.	Min.	Max.		
Α	11.80	12.20	0.465	0.480		
A1	8.90	9.10	0.350	0.358		
В	7.8	8.20	0.307	0.323		
С	0.75	0.85	0.030	0.033		
C2	1.95	2.05	0.077	0.081		
D	37.80	38.20	1.488	1.504		
D1	31.50	31.70	1.240	1.248		
Е	25.15	25.50	0.990	1.004		
E1	23.85	24.15	0.939	0.951		
E2	24.80) typ.	0.97	6 typ.		
G	14.90	15.10	0.587	0.594		
G1	12.60	12.80	0.496	0.504		
G2	3.50	4.30	0.138	0.169		
F	4.10	4.30	0.161	0.169		
F1	4.60	5.00	0.181	0.197		
Р	4.00	4.30	0.157	0.69		
P1	4.00	4.40	0.157	0.173		
S	30.10	30.30	1.185	1.193		

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

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Ordering information STTH20003TV

3 Ordering information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STTH20003TV	STTH20003TV	ISOTOP	27 g (without screws)	10 (with screws)	Tube

4 Revision history

Date	Revision	Description of Changes
1999	2C	First issue
5-Sep-2006	2	Reformatted to current standards. Thermal resistance updated in Table 2.

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